

Product Overview

SI4435DY: 30V P-Channel PowerTrench® MOSFET -8.8A, 20mΩ

For complete documentation, see the data sheet.

This P-Channel MOSFET is a rugged gate version of ON Semiconductor's advanced PowerTrench process. It has been optimized for power management applications requiring a wide range of gate drive voltage ratings (4.5V - 25V).

Features

- 8.8 A, -30 V & $R_{DS(ON)} = 20 \text{ m}\Omega$ @ $V_{GS} = -10 \text{ V}$; $R_{DS(ON)} = 35 \text{ m}\Omega$ @ $V_{GS} = -4.5 \text{ V}$
- Low gate charge (17nC typical)
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- High power and current handling capability

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{(BR)DSS}$ Min (V)	V_{GS} Max (V)	$V_{GS(th)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5 \text{ V}$ (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 4.5 \text{ V}$ (mΩ)	$R_{DS(on)}$ Max @ $V_{GS} = 10 \text{ V}$ (mΩ)	Q_g Typ @ $V_{GS} = 4.5 \text{ V}$ (nC)	Q_g Typ @ $V_{GS} = 10 \text{ V}$ (nC)	C_{ISS} Typ (pF)	Package Type
SI4435DY	0.3736	Pb-free Halide free non AEC-Q and PPAP	Active	P-Channel	Single	-30	20	-3	-8.8	2.5	-	35	20	-	17	1604	SOIC-8

For more information please contact your local sales support at www.onsemi.com.

Created on: 10/26/2021